



**ELECTRONICS, INC.**  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089

**NTE399**  
**Silicon NPN Transistor**  
**High Voltage Video Amp**  
**(Compl to NTE2366)**

**Absolute Maximum Ratings:**

Collector–Base Voltage, $V_{CBO}$ .....	300V
Collector–Emitter Voltage, $V_{CEO}$ .....	300V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$	
Continuous .....	100mA
Peak .....	300mA
Collector Power Dissipation, $P_C$ .....	900mW
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 200V, I_E = 0$	–	–	1.0	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 6V, I_C = 0$	–	–	1.0	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 10V, I_C = 5mA$	100	–	220	
Current Gain–Bandwidth Product	$f_T$	$V_{CB} = 30V, I_C = 10mA$	50	–	–	MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, f = 1MHz$	–	–	7.5	pF
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 2mA$	–	–	0.6	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20mA, I_B = 2mA$	–	–	1.0	V

